

• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. Two N Channel MOSFET inside.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Dual DIE in one package

• Application

- Mobile device battery charging and discharging
- Battery protection switch

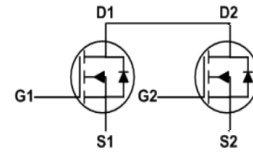
• Ordering Information:

Part NO.	ZMD68602D
Marking	ZMD68602
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

• Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ\text{C}}$	25	A
	$I_{D@TC=75^\circ\text{C}}$	19	A
	$I_{D@TC=100^\circ\text{C}}$	15.8	A
Pulsed Drain Current ^①	I_{DM}	75	A
Total Power Dissipation($TC=25^\circ\text{C}$)	$P_D@TC=25^\circ\text{C}$	50	W
Total Power Dissipation($TA=25^\circ\text{C}$)	$P_D@TA=25^\circ\text{C}$	1.25	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	75	mJ

• Product Summary



$V_{DS1} = 60V$

$V_{DS2} = 60V$

$R_{DS(ON)1} = 28m\Omega$

$R_{DS(ON)2} = 28m\Omega$

$I_{D1} = 25A$

$I_{D2} = 25A$



TO-252-4

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.3	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.8	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=12A$		28	34	m Ω
		$V_{GS}=4.5V, I_D=6A$		31	40	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=10A$		5		s
Source-drain voltage	V_{SD}	$I_S=12A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=25V$ $f = 1MHz$	-	1430	-	pF
Output capacitance	C_{oss}		-	160	-	
Reverse transfer capacitance	C_{rss}		-	115	-	

•Gate Charge characteristics($T_a = 25^{\circ}C$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$ $I_D = 5A$ $V_{GS} = 10V$	-	25	-	nC
Gate - Source charge	Q_{gs}		-	4	-	
Gate - Drain charge	Q_{gd}		-	9	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Maximum Continuous Drain Current

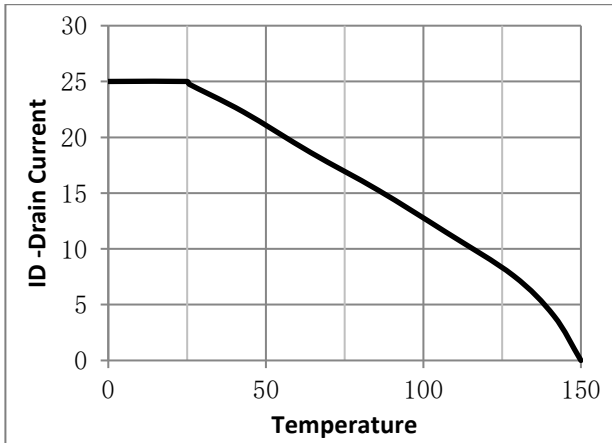


Fig.2 Typical output Characteristics

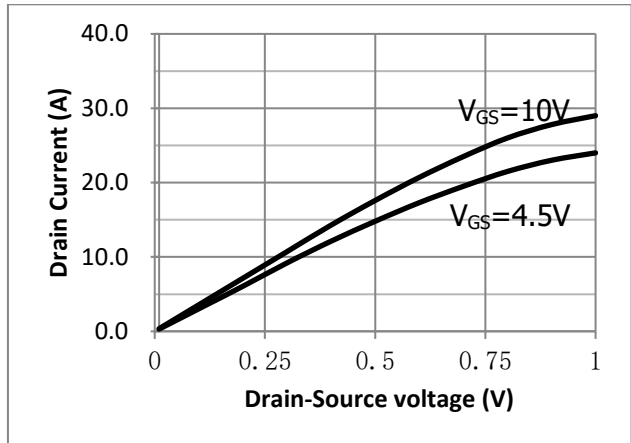


Fig.3 Threshold Voltage V.S Junction Temperature

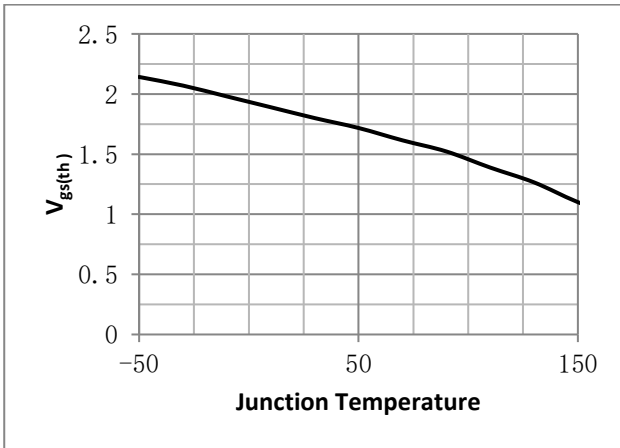


Fig.4 Resistance V.S Drain Current

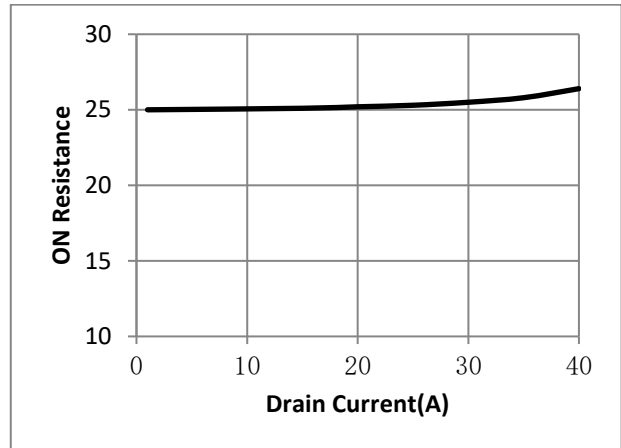


Fig.5 On-Resistance VS Gate Source Voltage

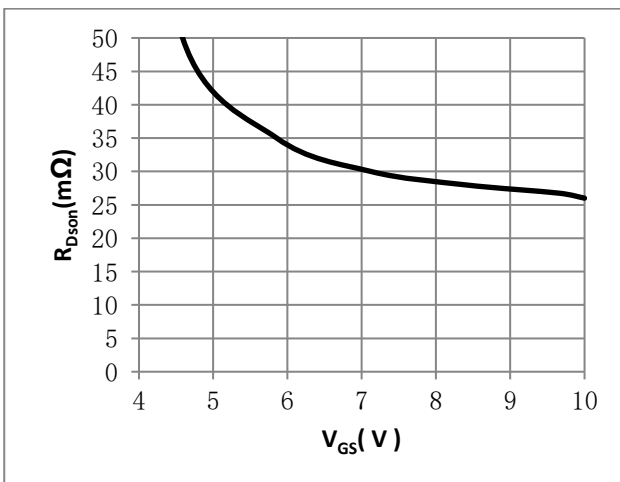
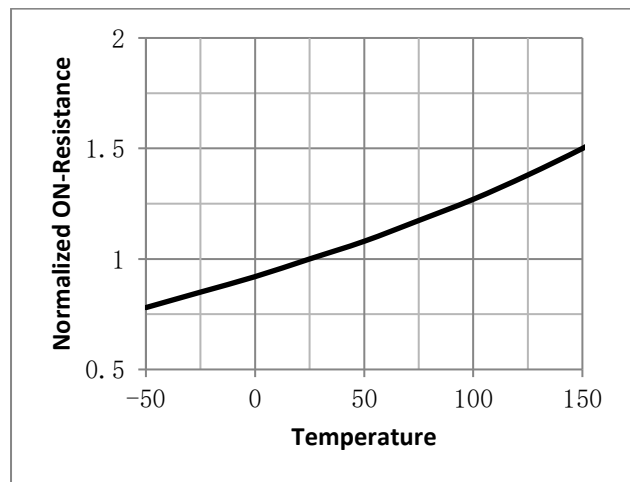


Fig.6 On-Resistance V.S Junction Temperature





●Dimensions(TO-252-4)

Unit: mm

